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DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

Device	V _{(BR)DSS}	R _{DS(ON) max}	I _{D MAX} T _A = +25°C
N-Channel	20V	$40m\Omega$ @ $V_{GS} = 4.5V$	4.7A
in-Chaine	200	$65m\Omega$ @ $V_{GS} = 2.5V$	3.7A

Description

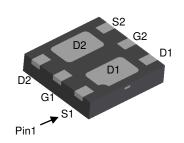
This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- Power Management Functions
- Portable Power Adaptors

U-DFN2020-6





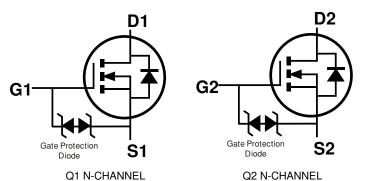
Bottom View

Features

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (4)
- Terminal Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2041UFDB -7	U-DFN2020-6	3,000/Tape & Reel
DMN2041UFDB -13	U-DFN2020-6	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

U-DFN2020-6



D7 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Year	201	4	2015		2016	20	17	2018		2019	2	2020
Code	В		С		D	Е	Ξ	F		G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	20	V	
Gate-Source Voltage		V_{GSS}	±12	V	
Continuous Drain Current (Note EVV 4 EV	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	4.7 3.8	Α
Continuous Drain Current (Note 5) V _{GS} = 4.5V	t < 5s	$T_A = +25$ °C $T_A = +70$ °C	I _D	6.1 4.9	Α
Maximum Continuous Body Diode Forward Curre	ent (Note 5)	I _S	2	Α	
Pulsed Drain Current (10μs pulse, duty cycle = 1	%)	I _{DM}	20	Α	

Thermal Characteristics

Characteristic		Symbol	Value	Units	
Total Dawar Dissipation (Note 5)	Steady State	D	1.4	W	
Total Power Dissipation (Note 5)	t < 5s	P_{D}	2.2		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		92		
Thermal Resistance, Junction to Ambient (Note 5)	t < 5s	$R_{ heta JA}$	55	°C/W	
Thermal Resistance, Junction to Case (Note 5)	$R_{ heta JC}$	30			
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to 150	°C	

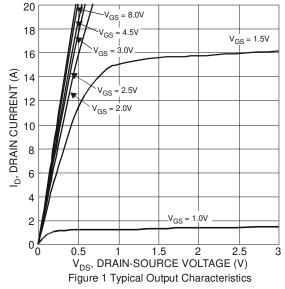
Electrical Characteristics Q1 N-CHANNEL (@TA = +25°C, unless otherwise specified.)

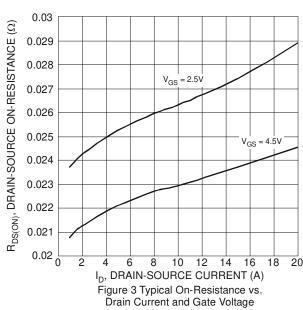
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)	•		•	•		
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1.0	μΑ	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						•
Gate Threshold Voltage	V _{GS(th)}	0.35	_	1.4	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance	В	_	23	40	mΩ	$V_{GS} = 4.5V, I_D = 4.2A$
Static Dialii-Source Off-nesistatice	R _{DS(ON)}	_	26	65	11122	$V_{GS} = 2.5V, I_D = 3.3A$
Diode Forward Voltage	V _{SD}	_	0.75	1.2	V	V _{GS} = 0V, I _S = 4.4A
DYNAMIC CHARACTERISTICS (Note 7)	<u>.</u>					
Input Capacitance	C _{iss}	_	713	_	pF	, , , , , , , , , , , , , , , , , , ,
Output Capacitance	Coss	_	80	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ - f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	68	_	pF	1 - 1.000112
Gate Resistance	R_g	_	15	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	0	_	8	_	nC	
Total Gate Charge (V _{GS} = 8V)	Qg	_	15	_	nC	V 40V I 55A
Gate-Source Charge	Q _{gs}	_	1.0	_	nC	$V_{DS} = 10V, I_D = 5.5A$
Gate-Drain Charge	Q _{gd}	_	1.1	_	nC	
Turn-On Delay Time	t _{D(on)}	_	3.6	_	ns	
Turn-On Rise Time	tr	_	15.9	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(off)}	_	16.0	_	ns	$R_L = 2.3\Omega$, $R_G = 1\Omega$
Turn-Off Fall Time	t _f	_	2.6	_	ns	
Body Diode Reverse Recovery Time	trr	_	6.6	_	nS	$I_S = 4.4A$, $dI/dt = 100A/\mu s$
Body Diode Reverse Recovery Charge		_	1.2	_	nC	I _S = 4.4A, dI/dt = 100A/µs

5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing. Notes:









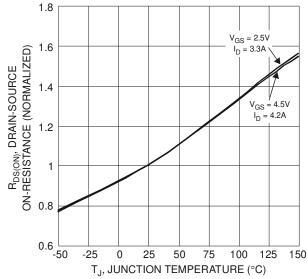
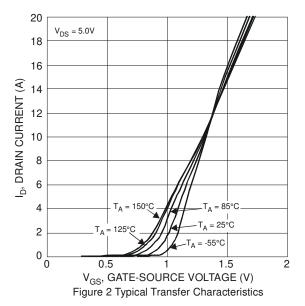
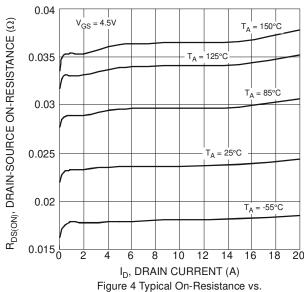
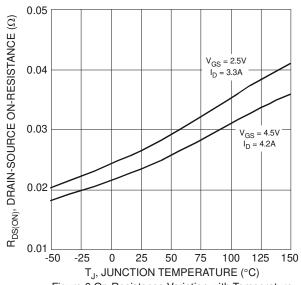


Figure 5 On-Resistance Variation with Temperature







Drain Current and Temperature

Figure 6 On-Resistance Variation with Temperature



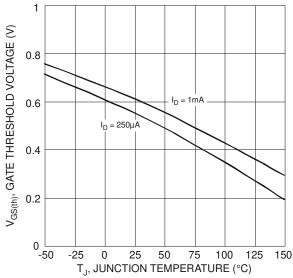
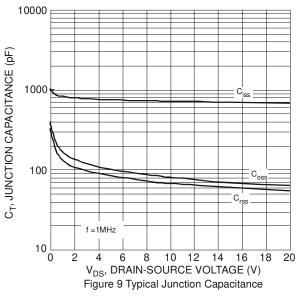
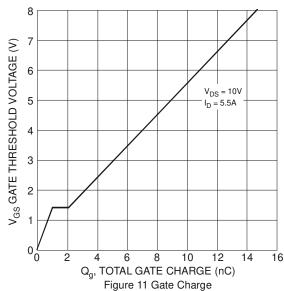
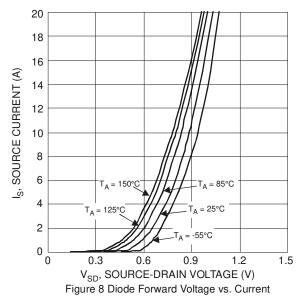
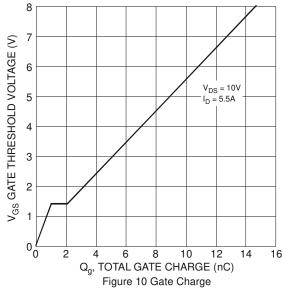


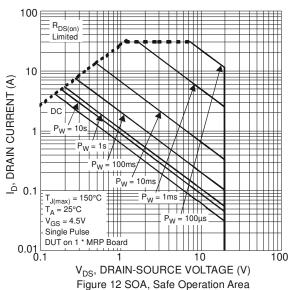
Figure 7 Gate Threshold Variation vs. Ambient Temperature



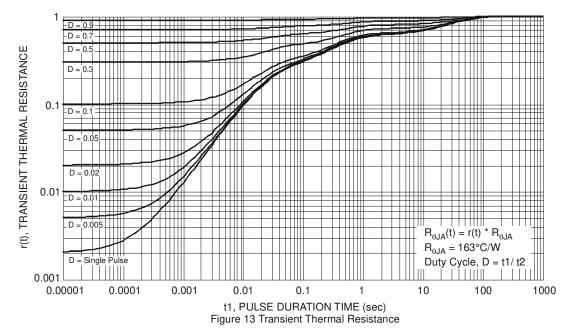






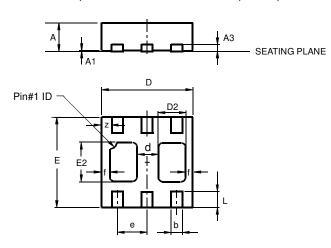






Package Outline Dimensions

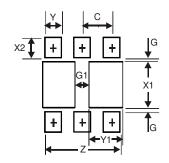
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



U-DFN2020-6							
Type B							
Dim	Min Max Typ						
Α	0.545	0.605	0.575				
A 1	0	0.05	0.02				
A 3	_	_	0.13				
b	0.20	0.30	0.25				
D	1.95	2.075	2.00				
d			0.45				
D2	0.50	0.70	0.60				
е			0.65				
E	1.95	2.075	2.00				
E2	0.90	1.10	1.00				
f	_	_	0.15				
L	0.25	0.35	0.30				
Z			0.225				
All I	All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	1.67
G	0.20
G1	0.40
X1	1.0
X2	0.45
Υ	0.37
Y1	0.70
С	0.65



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